

# HITTIE MICROWAVE CORPORATION

# HMC165S14

#### GaAS MMIC SP4T SWITCH DC TO 2.0 GHz

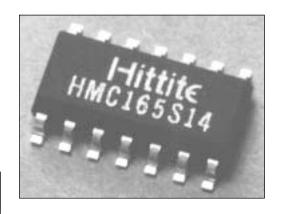
FEBRUARY 2001 V01.0101

#### **Features**

LOW INSERTION LOSS: 0.4dB

INTEGRATED 2:4 DECODER

14 LEAD SOIC PACKAGE



# General Description

The HMC165S14 is a low-cost SP4T switch in a 14-lead SOIC package for use in antenna diversity, switched filter banks, gain/attenuation selection, and general channel multiplexing applications. The switch can control signals up to 2.5 GHz and is especially suited for 800-1000 MHz basestation applications\*. A 2:4 decoder is integrated on the switch, requiring only 2 control lines and a negative bias to select each RF path. Switch outputs are reflective shorts when "Off". The 2:4 decoder replaces 4 to 8 control lines normally required by GaAS SP4T switches. See positive bias/TTL SP4T HMC241QS16.

### **Guaranteed Performance**

For 0/-5V Control and Vee = -5V in a 50 Ohm System, -40 to +85 deg C

Parameter	Frequency	Min.	Тур.	Max.	Units
Insertion Loss	DC - 0.5GHz DC - 1.0GHz DC - 2.0GHz		0.3 0.5 1.0	0.6 0.8 1.3	dB dB dB
Isolation	DC -0.5GHz DC - 1.0GHz DC - 2.0GHz	35 28 20	39 32 24		dB dB dB
Return Loss	DC -1.0GHz DC - 2.0GHz	16 8.5	20 11		dB dB
Input Power for 1dB Compression	50 MHz 0.5 - 2.0GHz		22 24		dBm
Input Third Order Intercept	50 MHz 0.5 - 2.0GHz		35 42		dBm
Switching Characteristics tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)	DC - 2.0GHz		25 50		ns ns

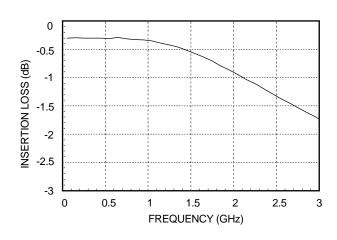




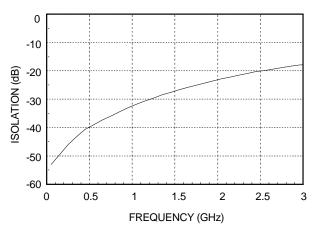
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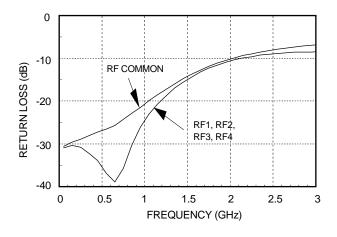
#### **Insertion Loss**



#### Isolation



#### Return Loss





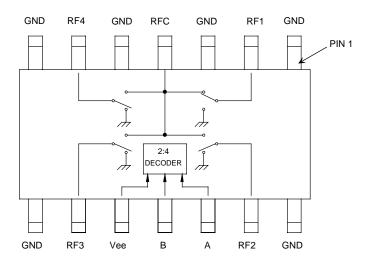




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# Functional Diagram



# Absolute Maximum Ratings

Bias Voltage Range (Port Vee)	-7.0 Vdc
Control Voltage Range (A & B)	Vee -0.5V to +1.0 Vdc
Storage Temperature	-65 to +150 deg C
Operating Temperature	-40 to +85 deg C
Maximum Input Power	+27dBm (<500MHz) +30dBm (>500MHz)

# Bias Voltage & Current

Vee Range = -5.0 Vdc ± 10%		
Vee (Vdc)	lee (Typ.) (mA)	lee (Max.) (mA)
-5.0	3.0	6.0

# Truth Table

Control Input		Signal Path State	
Α	В	RFCOM to:	
High	High	RF1	
Low	High	RF2	
High	Low	RF3	
Low	Low	RF4	

# **Control Voltages**

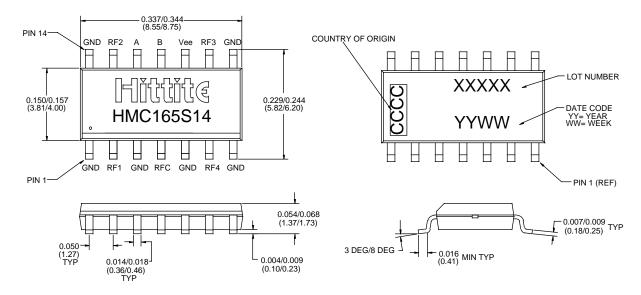
State	Bias Condition
Low	0 to -3 VDC @ 220uA Typ.
High	Vee +0.8 VDC @ 100uA Max.



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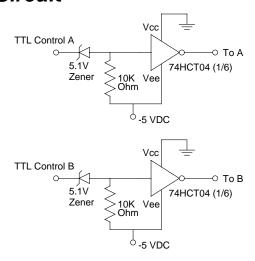
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#### **Outline**



- 1) MATERIAL:
  - A) PACKAGE BODY LOW STRESS INJECTION MOLDED PLASTIC, SILICA & SILICONE IMPREGNATED B) LEADFRAME MATERIAL: COPPER ALLOY
- 2. PLATING: LEAD-TIN SOLDER PLATE
- 3. DIMENSIONS ARE IN INCHES (MILLIMETERS) UNLESS OTHERWISE SPECIFIED TOL. ARE ±0.005(±0.13)

## TTL Interface Circuit



#### Note:

Control inputs A and B can be driven directly with TTL logic with -5 Volts applied to the HCT logic gates (Vee) and to Vee (pin 10) of the RF switch.